

Structure and Method for Forming the Gate Electrode in a Multiple-Gate Transistor

ABSTRACT OF THE DISCLOSURE

In a method of forming semiconductor device, a semiconductor fin is formed on a semiconductor-on-insulator substrate. A gate dielectric is formed over at least a portion of the semiconductor fin. A first gate electrode material is formed over the gate dielectric and a second gate electrode material is formed over the first gate electrode material. The second gate electrode material is planarized and then etched selectively with respect to first gate electrode material. The first gate electrode material can then be etched.